

GigaDevice Semiconductor Inc.

GDSCN832xx

Datasheet

Revision 1.0

(Nov. 2024)

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1. General description

The GDSCN is a 2/3-port EtherCAT SubDevice controller with dual integrated Ethernet PHY which contain a full duplex 100BASE-TX transceiver and support 100Mbps (100BASE-TX) operation. The GDSCN supports HP Auto-MDIX, allowing the use of direct connect or cross-over LAN cables.

The GDSCN includes an EtherCAT SubDevice controller with 8K bytes of Process Data RAM(PDRAM) and 8 Fieldbus Memory Management Units (FMMUs). Each FMMU performs the task of mapping logical addresses to physical addresses. The EtherCAT SubDevice controller also includes 8 SyncManagers to allow the exchange of data between the EtherCAT main and the local application. Each SyncManager's direction and mode of operation is configured by the EtherCAT main. Two modes of operation are available: buffered mode or mailbox mode. In the buffered mode, both the local microcontroller and EtherCAT main can write to the device concurrently. The buffer within the GDSCN will always contain the latest data. If newer data arrives before the old data can be read out, the old data will be dropped. In mailbox mode, access to the buffer by the local microcontroller and the EtherCAT main is performed using handshakes, guaranteeing that no data will be dropped.

2. Device overview

2.1. Device information

Table 2-1. GDSCN devices features and peripheral list

Feature	GDSCN
Ports	3 ports(2PHYs,1MII)
FMMUs	8
SyncManagers	8
Process data RAM(PDRAM)	8KB
Distributed Clocks	64bit
Process Data Interfaces	Digital I/O On-chip bus(SPI,EXMC)
Power supply	1.1V Integrated voltage regulator for logic core/ 2.5V Ethernet magnetics/ 3.3V power supply voltage
I/O	1.8V~3.3V compatible I/O

2.2. Block diagram

Figure 2-1. GDSCN system diagram

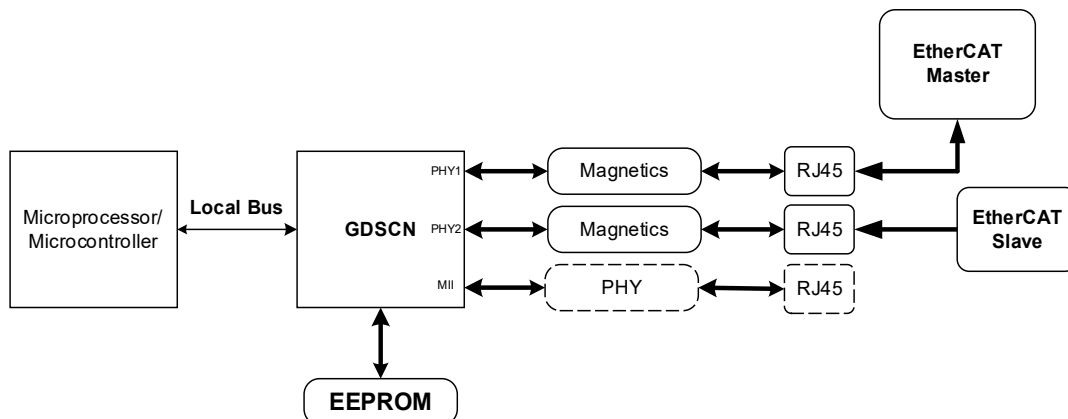
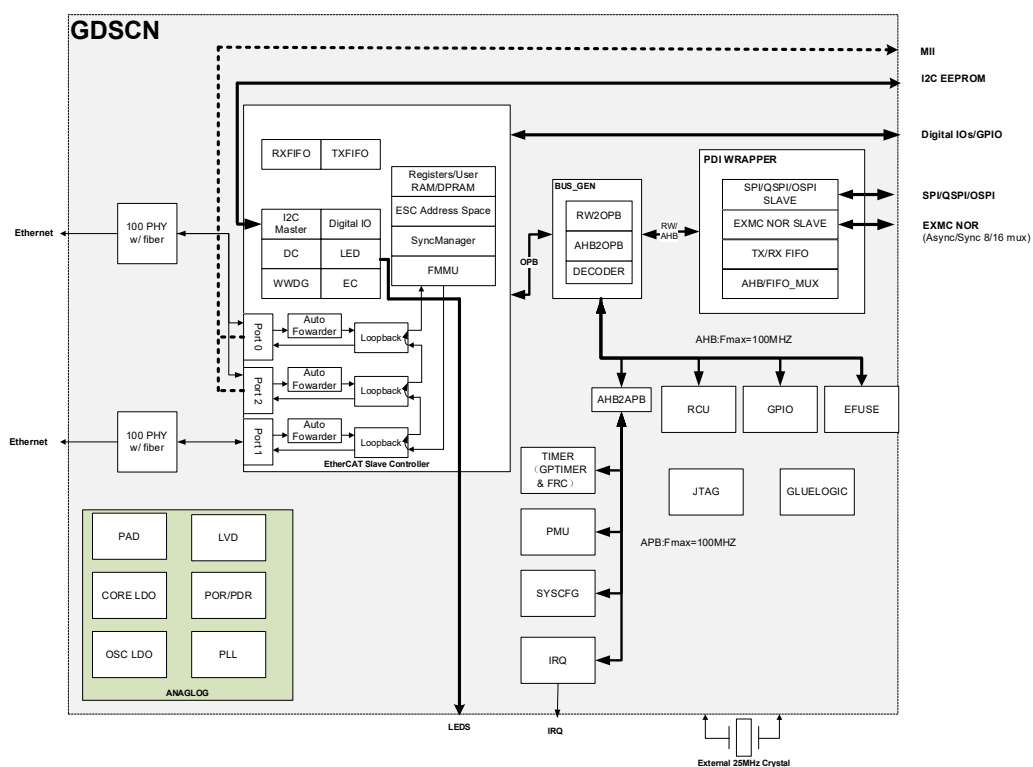
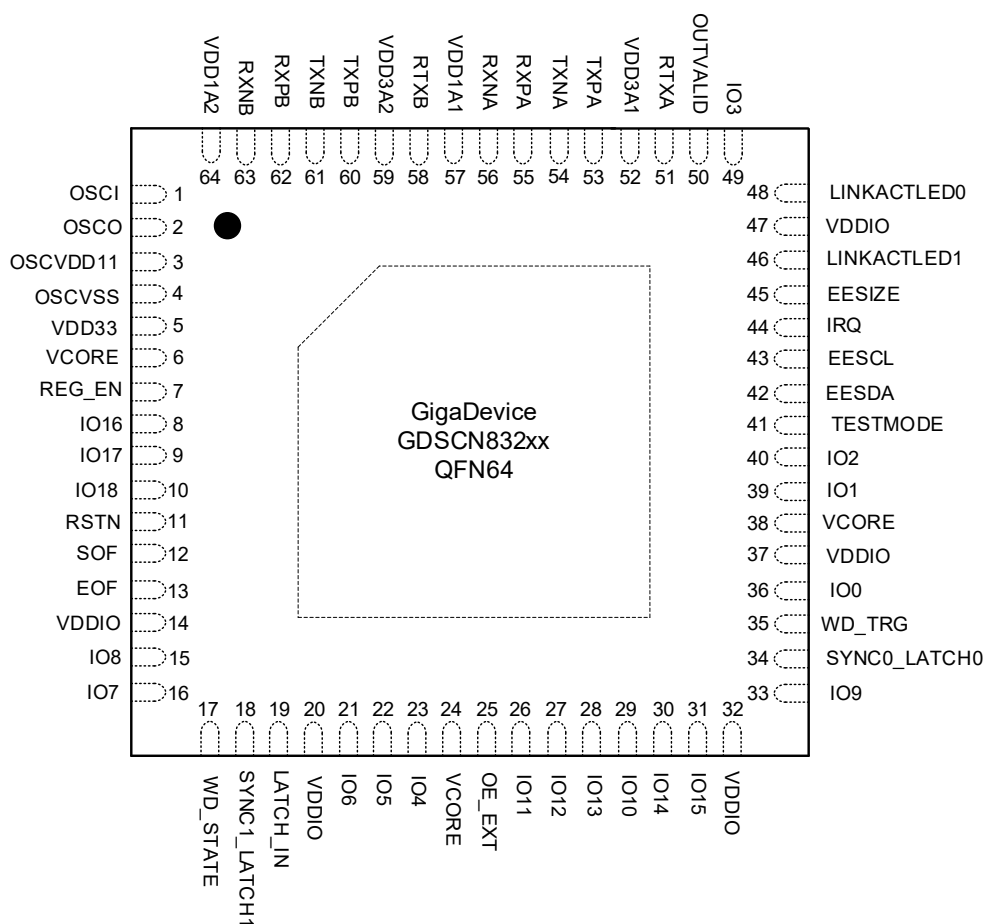


Figure 2-2. GDSCN block diagram



2.3. Pinouts and pin assignment

Figure 2-3. GDSCN QFN64 pinouts



2.4. Memory map

Table 2-2. GDSCN memory map

Pre-defined Regions	Address	Peripherals
EtherCAT	0x0000	Type
	0x0001	Revision
	0x0002 - 0x0003	Build
	0x0004	FMMUs Supported
	0x0005	SyncManagers Supported
	0x0006	RAM Size
	0x0007	Port Descriptor
	0x0008 - 0x0009	ESC Features Supported

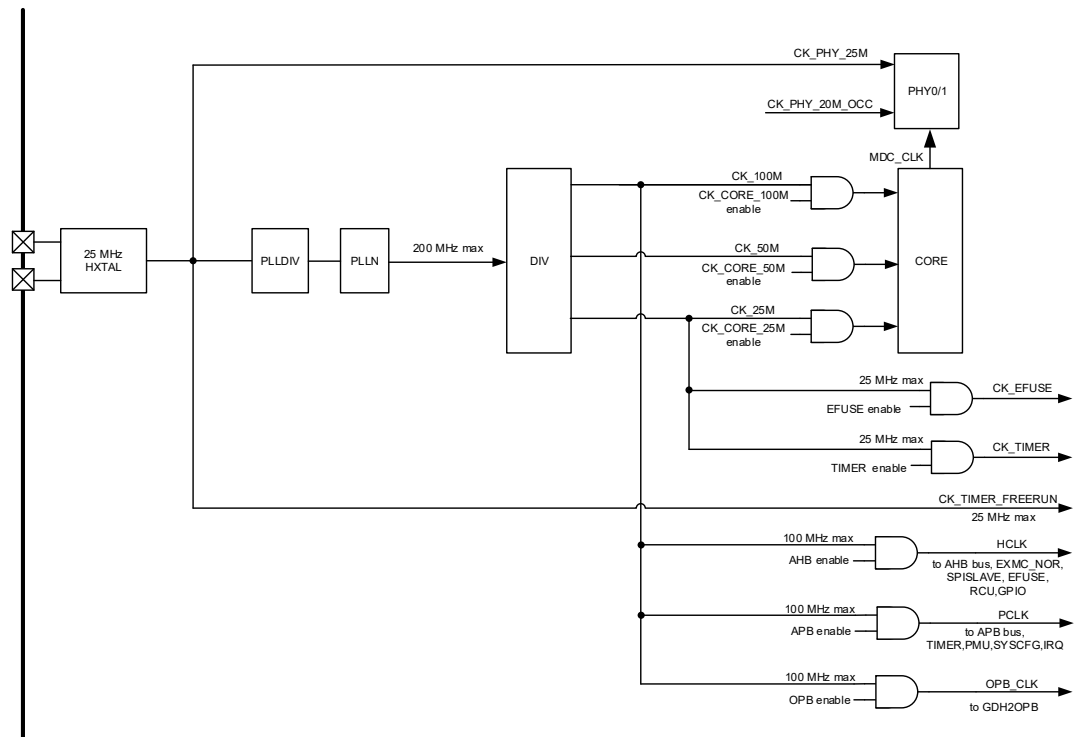
Pre-defined Regions	Address	Peripherals
	0x0010 - 0x0011	Configured Station Address
	0x0012 - 0x0013	Configured Station Alias
	0x0013 - 0x001F	Reserved
	0x0020	Write Register Enable
	0x0021	Write Register Protection
	0x0022 - 0x002F	Reserved
	0x0030	ESC Write Enable
	0x0031	ESC Write Protection
	0x0032 - 0x003F	Reserved
	0x0040	ESC Reset ECAT
	0x0041	ESC Reset PDI
	0x0042 - 0x00FF	Reserved
	0x0100 - 0x0103	ESC DL Control
	0x0104 - 0x0107	Reserved
	0x0108 - 0x0109	Physical Read/Write Offset
	0x0110 - 0x0111	ESC DL Status
	0x0112 - 0x011F	Reserved
	0x0120 - 0x0121	AL Control
	0x0122 - 0x012F	Reserved
	0x0130 - 0x0131	AL Status
	0x0132 - 0x0133	Reserved
	0x0134 - 0x0135	AL Status Code
	0x0136 - 0x0137	Reserved
	0x0138	RUN LED Override
	0x0139	Reserved
	0x0140	PDI Control
	0x0141	ESC Configuration
	0x0142 - 0x0143	ASIC Configuration
	0x0144 - 0x0145	RESERVED Register
	0x0146 - 0x014F	Reserved
	0x0150	PDI Configuration
	0x0151	Sync/Latch PDI Configuration
	0x0152 - 0x0153	Extended PDI Configuration
	0x0154 - 0x01FF	Reserved
	0x0200 - 0x0201	ECAT Event Mask
	0x0202 - 0x0203	Reserved
	0x0204 - 0x0207	PDI AL Event Mask
	0x0208 - 0x0209	Reserved
	0x0210 - 0x0211	ECAT Event Request
	0x0212 - 0x021F	Reserved

Pre-defined Regions	Address	Peripherals
	0x0220 - 0x0223	AL Event Request
	0x0223 - 0x022F	Reserved
	0x0300 - 0x0307	RX Error Counter
	0x0308 - 0x030B	Forwarded RX Error Counter
	0x030C	ECAT Processing Unit Error Counter
	0x030D	PDI Error Counter
	0x030E	PDI Error Code
	0x030F	Reserved
	0x0310 - 0x0313	Lost Link Counter
	0x0314 - 0x03FF	Reserved
	0x0400 - 0x0401	Watchdog Divider
	0x0410 - 0x0411	Watchdog Time PDI
	0x0420 - 0x0421	Watchdog Time Process Data
	0x0440 - 0x0441	Watchdog Status Process Data
	0x0442	Watchdog Counter Process Data
	0x0443	Watchdog Counter PDI
	0x0444 - 0x04FF	Reserved
	0x0500	EEPROM Configuration
	0x0501	EEPROM PDI Access State
	0x0502 - 0x0503	EEPROM Control/Status
	0x0504 - 0x0507	EEPROM Address
	0x0508 - 0x050B	EEPROM Data
	0x050C - 0x050F	Reserved
	0x0510 - 0x0511	MII Management Control/Status
	0x0512	PHY Address
	0x0513	PHY Register Address
	0x0514 - 0x0515	PHY DATA
	0x0516	MII Management ECAT Access State
	0x0517	MII Management PDI Access State
	0x0518 - 0x051B	PHY Port Status
	0x051C - 0x05FF	Reserved
	0x0600 - 0x06FF	FMMU
	0x0700 - 0x07FF	Reserved
	0x0800 - 0x087F	SyncManager
	0x0880 - 0x08FF	Reserved
	0x0900 - 0x09FF	Distributed Clocks (DC)
	0x0A00 - 0x0AFF	Reserved
	0x0E00 - 0x0E07	Product ID
	0x0E08 - 0x0E0F	Vendor ID
	0x0E10 - 0x0EFF	Reserved

Pre-defined Regions	Address	Peripherals
	0x0F00 - 0x0F03	Digital I/O Output Data
	0x0F04 - 0x0F0F	Reserved
	0x0F10 - 0x0F17	General Purpose Outputs
	0x0F18 - 0x0F1F	General Purpose Inputs
	0x0F20 - 0x0F7F	Reserved
	0x0F80 - 0x0FFF	User RAM
	0x1000 - 0x2FFF	Process Data RAM
Peripheral	0x3300 - 0x33FF	AHB2OPB Bridge
	0x3400 - 0x34FF	RCU
	0x3500 - 0x35FF	GPIO
	0x3600 - 0x36FF	EFUSE
	0x3700 - 0x37FF	PMU
	0x3800 - 0x38FF	TIMER
	0x3900 - 0x39FF	SYSCFG
	0x3A00 - 0x3AFF	IRQ

2.5. Clock tree

Figure 2-4. GDSCN clock tree



Legend:

HXTAL: High speed crystal oscillator

2.6. Pin definitions

2.6.1. GDSCN QFN64 pin definitions

Table 2-3. GDSCN QFN64 pin definitions

QFN64				
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
OSCI	1			Default: OSCI
OSCO	2			Default: OSCO
OSCVDD11	3	P	-	Default: OSCVDD11
OSCVSS	4	P	-	Default: OSCVSS
VDD33	5	P	-	Default: VDD33
VCORE	6	P	-	Default: VCORE
REG_EN	7	I/O	5VT	Default: REG_EN Additional: REG_EN
IO16	8	I/O	5VT	Default: IO16 Alternate: SIO4, MCU_PDI_TYPE Additional: VBG11
IO17	9	I/O	5VT	Default: IO17 Alternate: SIO5, EFUSE_LDO_BYP
IO18	10	I/O	5VT	Default: IO18 Alternate: SIO6, PHYRST_MODE
RSTN	11	I/O		Default: RSTN Additional: RSTN
SOF	12	I/O	5VT	Default: SOF Alternate: EXMC_AD2, PDI_DIGIO_SOF, SIO2
EOF	13	I/O	5VT	Default: EOF Alternate: EXMC_AD1, PDI_DIGIO_EOF, SIO1
VDDIO	14	P		Default: VDDIO
IO8	15	I/O	5VT	Default: IO8 Alternate: EXMC_AD14, PDI_DIGIO8, PDI_GPIO8, MII0_TXD3, MII2_TXD3, TX_SHIFT1
IO7	16	I/O	5VT	Default: IO7 Alternate: EXMC_AD13, PDI_DIGIO7, PDI_GPIO7, MII0_TXD2, MII2_TXD2, TX_SHIFT0
WD_STATE	17	I/O	5VT	Default: WD_STATE Alternate: EXMC_AD0, PDI_DIGIO_WD_STATE, SIO0
SYNC1_LATCH1	18	I/O	5VT	Default: SYNC1_LATCH1 Alternate: SYNC1, LATCH1
LATCH_IN	19	I/O	5VT	Default: LATCH_IN Alternate: EXMC_AD9, PDI_DIGIO_LATCH_IN, SCK

QFN64				
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
VDDIO	20	P	-	Default: VDDIO
IO6	21	I/O	5VT	Default: IO6 Alternate: EXMC_AD12, PDI_DIGIO6, PDI_GPIO6, MII0_TXD1, MII2_TXD1
IO5	22	I/O	5VT	Default: IO5 Alternate: EXMC_AD11, PDI_DIGIO5, PDI_GPIO5, MII0_TXD0, MII2_TXD0
IO4	23	I/O	5VT	Default: IO4 Alternate: EXMC_AD10, PDI_DIGIO4, PDI_GPIO4, MII0_TX_EN, MII2_TX_EN
VCORE	24	P	-	Default: VCORE Additional: VDDCR
OE_EXT	25	I/O	5VT	Default: OE_EXT Alternate: EXMC_NL, PDI_DIGIO_OE_EXT, MII_CLK25, SIO7
IO11	26	I/O	5VT	Default: IO11 Alternate: EXMC_CLK, PDI_DIGIO11, PDI_GPIO11, MII2_RX_DV, MII0_RX_DV
IO12	27	I/O	5VT	Default: IO12 Alternate: EXMC_NWAIT, PDI_DIGIO12, PDI_GPIO12, MII0_RXD0, MII2_RXD0
IO13	28	I/O	5VT	Default: IO13 Alternate: EXMC_NE, PDI_DIGIO13, PDI_GPIO13, MII0_RXD1, MII2_RXD1
IO10	29	I/O	5VT	Default: IO10 Alternate: PDI_DIGIO10, PDI_GPIO10, MII0_LINKPOL, LINKACTLED2
IO14	30	I/O	5VT	Default: IO14 Alternate: EXMC_NWE, PDI_DIGIO14, PDI_GPIO14, MII0_RXD2, MII2_RXD2
IO15	31	I/O	5VT	Default: IO15 Alternate: EXMC_NOE, PDI_DIGIO15, PDI_GPIO15, MII0_RXD3, MII2_RXD3
VDDIO	32	P	-	Default: VDDIO
IO9	33	I/O	5VT	Default: IO9 Alternate: EXMC_AD15, PDI_DIGIO9, PDI_GPIO9, MII0_RX_ER, MII2_RX_ER
SYNC0_LATCH0	34	I/O	5VT	Default: SYNC0_LATCH0 Alternate: SYNC0, LATCH0
WD_TRIG	35	I/O	5VT	Default: WD_TRIG Alternate: EXMC_AD3, PDI_DIGIO_WD_TRIG, SIO3
IO0	36	I/O	5VT	Default: IO0 Alternate: EXMC_AD6, PDI_DIGIO0, PDI_GPIO0, MII0_RX_CLK, MII2_RX_CLK

QFN64				
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
VDDIO	37	P	-	Default: VDDIO Additional: VDDIO
VCORE	38	P	-	Default: VCORE Additional: VDDCR
IO1	39	I/O	5VT	Default: IO1 Alternate: EXMC_AD7, PDI_DIGIO1, PDI_GPIO1, MII_CLK
IO2	40	I/O	5VT	Default: IO2 Alternate: EXMC_AD8, PDI_DIGIO2, PDI_GPIO2, MII_DATA
TESTMODE	41	I/O	5VT	Default: TESTMODE Alternate: TESTMODE
EESDA	42	I/O	5VT	Default: EESDA Alternate: EEPROM_DATA, JTAG_TMS
EESCL	43	I/O	5VT	Default: EESCL Alternate: EEPROM_CLK, JTAG_TCK
IRQ	44	I/O	5VT	Default: IRQ Alternate: IRQ
EESIZE	45	I/O	5VT	Default: EESIZE Alternate: EEPROM_SIZE, RUNLED
LINKACTLED1	46	I/O	5VT	Default: LINKACTLED1 Alternate: LINKACTLED1, JTAG_TDI, CHIP_MODE1
VDDIO	47	P	-	Default: VDDIO Additional: VDDIO
LINKACTLED0	48	I/O	5VT	Default: LINKACTLED0 Alternate: LINKACTLED0, JTAG_TDO, CHIP_MODE0
IO3	49	I/O	5VT	Default: IO3 Alternate: EXMC_AD4, PDI_DIGIO3, PDI_GPIO3, MII2_LINK, MII0_LINK Additional: VCORE_REF
OUTVALID	50	I/O	5VT	Default: OUTVALID Alternate: EXMC_AD5, PDI_DIGIO_OUTVALID, SCS
RTXA	51	I/O		Default: RTXA Additional: RTX_P1
VDD3A1	52	P	-	Default: VDD3A1 Additional: VDA3PL_P1
TXPA	53	I/O		Default: TXPA Additional: TXP_P1
TXNA	54	I/O		Default: TXNA Additional: TXN_P1
RXPA	55	I/O		Default: RXPA Additional: RXP_P1

QFN64				
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
RXNA	56	I/O		Default: RXNA Additional: RXN_P1
VDD1A1	57	P	-	Default: VDD1A1 Additional: VDD1A_P1
RTXB	58	I/O		Default: RTXB Additional: RTX_P2
VDD3A2	59	P	-	Default: VDD3A2 Additional: VDA3PL_P2
TXPB	60	I/O		Default: TXPB Additional: TXP_P2
TXNB	61	I/O		Default: TXNB Additional: TXN_P2
RXPB	62	I/O		Default: RXPB Additional: RXP_P2
RXNB	63	I/O		Default: RXNB Additional: RXN_P2
VDD1A2	64	P	-	Default: VDD1A2 Additional: VDD1A_P2

Notes:

(1) Type: I = input, O = output, P = power.

(2) I/O Level: 5VT = 5 V tolerant.

2.6.2. GDSCN pin alternate functions

Table 2-4. GDSCN alternate functions summary

Pin Name	EXMC	Digital IO	OSPI (8-wire) + GPIO	QSPI (4-wire) + MII (4-wire)	QSPI (4-wire) + MII
IO16	MCU_PDITY PE	MCU_PDITYPE	SIO4/ MCU_PDITY PE	MCU_PDITY PE	MCU_PDITYPE
IO17	EFUSE_LDO _BYP	EFUSE_LDO_BYP	SIO5/ EFUSE_LDO _BYP	EFUSE_LDO _BYP	EFUSE_LDO_BYP
IO18	PHYRST_M ODE	PHYRST_MODE	SIO6/ PHYRST_M ODE	PHYRST_M ODE	PHYRST_MODE
RSTn	RSTn	RSTn	RSTn	RSTn	RSTn
SOF	EXMC_AD2	PDI_DIGIO_SOF	SIO2	SIO2	SIO2
EOF	EXMC_AD1	PDI_DIGIO_EOF	SIO1	SIO1	SIO1
IO8	EXMC_AD14	PDI_DIGIO8	PDI_DIGIO8	MII2_TXD3/ TX_SHIFT1	MII0_TXD3/ TX_SHIFT1
IO7	EXMC_AD13	PDI_DIGIO7	PDI_DIGIO7	MII2_TXD2/	MII0_TXD2/

Pin Name	EXMC	Digital IO	OSPI (8-wire) + GPIO	QSPI (4-wire) + MII (4-wire)	QSPI (4-wire) + MII
				TX_SHIFT0	TX_SHIFT0
WD_STATE	EXMC_AD0	PDI_DIGIO_WD_STATE	SIO0	SIO0	SIO0
SYNC1_LATCH1	SYNC1/LATCH1	SYNC1/LATCH1	SYNC1/LATCH1	SYNC1/LATCH1	SYNC1/LATCH1
LATCH_IN	EXMC_AD9	PDI_DIGIO_LATCH_IN	SCK	SCK	SCK
IO6	EXMC_AD12	PDI_DIGIO6	PDI_DIGIO6	MII2_TXD1	MII0_TXD1
IO5	EXMC_AD11	PDI_DIGIO5	PDI_DIGIO5	MII2_TXD0	MII0_TXD0
IO4	EXMC_AD10	PDI_DIGIO4	PDI_DIGIO4	MII2_TX_EN	MII0_TX_EN
OE_EXT	EXMC_NL	PDI_DIGIO_OE_EXT	SIO7	MII_CLK25	MII_CLK25
IO11	EXMC_CLK	PDI_DIGIO11	PDI_GPIO11	MII2_RX_DV	MII0_RX_DV
IO12	EXMC_NWAIT	PDI_GPIO12	PDI_GPIO12	MII2_RXD0	MII0_RXD0
IO13	EXMC_NE	PDI_GPIO13	PDI_GPIO13	MII2_RXD1	MII0_RXD1
IO10		PDI_GPIO10	PDI_GPIO10	MII_LINKPOL / LINKACTLED2	MII_LINKPOL / LINKACTLED2
IO14	EXMC_NWE	PDI_GPIO14	PDI_GPIO14	MII2_RXD2	MII0_RXD2
IO15	EXMC_NOE	PDI_GPIO15	PDI_GPIO15	MII2_RXD3	MII0_RXD3
IO9	EXMC_AD15	PDI_GPIO9	PDI_GPIO9	MII2_RX_ER	MII0_RX_ER
SYNC0_LATCH0	SYNC0/LATCH0	SYNC0/LATCH0	SYNC0/LATCH0	SYNC0/LATCH0	SYNC0/LATCH0
WD_TRIG	EXMC_AD3	PDI_DIGIO_WD_TRIG	SIO3	SIO3	SIO3
IO0	EXMC_AD6	PDI_DIGIO0	PDI_DIGIO0	MII2_RX_CLK	MII0_RX_CLK
IO1	EXMC_AD7	PDI_DIGIO1	PDI_DIGIO1	MII_CLK	MII_CLK
IO2	EXMC_AD8	PDI_DIGIO2	PDI_DIGIO2	MII_DATA	MII_DATA
TESTMODE	TESTMODE	TESTMODE	TESTMODE	TESTMODE	TESTMODE
EESDA	EEPROM_DATA / JTAG_TMS	EEPROM_DATA/JTAG_TMS	EEPROM_DATA / JTAG_TMS	EEPROM_DATA / JTAG_TMS	EEPROM_DATA/JTAG_TMS
EESCL	EEPROM_CLK / JTAG_TCK	EEPROM_CLK / JTAG_TCK	EEPROM_CLK / JTAG_TCK	EEPROM_CLK / JTAG_TCK	EEPROM_CLK / JTAG_TCK
IRQ	IRQ	IRQ	IRQ	IRQ	IRQ
EESIZE	EEPROM_SIZE	EEPROM_SIZE/RU	EEPROM_SIZE	EEPROM_SIZE	EEPROM_SIZE/RU

Pin Name	EXMC	Digital IO	OSPI (8-wire) + GPIO	QSPI (4-wire) + MII (4-wire)	QSPI (4-wire) + MII
	ZE/ RUNLED	NLED	ZE/ RUNLED	ZE/ RUNLED	NLED
LINKACTLED1	LINKACTLED1/ JTAG_TDI/ CHIP_MODE1	LINKACTLED1/ JTAG_TDI/ CHIP_MODE1	LINKACTLED1/ JTAG_TDI/ CHIP_MODE1	LINKACTLED1/ JTAG_TDI/ CHIP_MODE1	LINKACTLED1/ JTAG_TDI/ CHIP_MODE1
LINKACTLED0	LINKACTLED0/ JTAG_TDO/ CHIP_MODE0	LINKACTLED0/ JTAG_TDO/ CHIP_MODE0	LINKACTLED0/ JTAG_TDO/ CHIP_MODE0	LINKACTLED0/ JTAG_TDO/ CHIP_MODE0	LINKACTLED0/ JTAG_TDO/ CHIP_MODE0
IO3	EXMC_AD4	PDI_DIGIO3	PDI_GPIO3	MI12_LINK	MI10_LINK
OUTVALID	EXMC_AD5	PDI_DIGIO_OUTVALID	SCS	SCS	SCS

3. Functional description

3.1. EtherCAT SubDevice Controller(ESC)

- Port support: 2 internal phy port and 1 external MII.
- 8 Fieldbus Memory Management Units (FMMUs).
- 8KB PDRAM.
- 64-bit distributed clock, support allows synchronization with other EtherCAT devices.
- 8 Syncmanager entities.
- DC synchronization less than 1us.

The EtherCAT SubDevice Controller (ESC), licensed from Beckhoff Automation, It takes care of the EtherCAT communication as an interface between the EtherCAT fieldbus and the sub application.

3.2. Clock, reset and supply management

- Supports 25Mhz HSE clock.
- PLL: 25Mhz 8x frequency to achieve 200Mhz clock
- System clock: PLL 2 frequency division, fixed 100Mhz
- AHB/APB clock: Fixed 100Mhz
- Other normally open clock: 50Mhz, 25Mhz free running clock, for special functions
- 1.1 to 3.3V application supply and I/Os.

The Clock Control Unit (CCU) provides an external High Speed crystal oscillator (HXTAL) and a phase-locked loop (PLL). This clock is usually provided by the OSCIN and OSCOUT of the passive 25MHz crystal oscillator or by the OSCIN pin of the single-ended 25MHz clock source driver. See [Figure 2-4. GDSCN clock tree](#) for details on the clock tree.

The Reset Control Unit (RCU) controls two kinds of reset: system reset and module reset. System reset includes power-on reset (POR), external pin reset (NRST) and EtherCAT system reset, which can reset all circuits in the device. Module reset includes digital reset, PHY reset and EtherCAT core reset, which can reset each corresponding module.

Power supply schemes:

- V_{DDIO} range: 1.8 to 3.3 V, external power supply for I/Os. Provided externally through VDDIO pins.
- V_{DD33}, V_{DD3A1}, V_{DD3A2}: 3.3 V, external power supplies for Internal 1.1V Core Regulator and 1.1V Oscillator Regulator, PHYA and PHYB.
- V_{CORE}, V_{DD1A1}, V_{DD1A2}: 1.1 V, power supply for I/Os, Core logic and PHY digital, PHYA and PHYB.

3.3. General-purpose inputs/outputs (GPIOs)

- Up to 35 GPIOs, 8 kinds of communication modes to can be choose
- Analog input/output configurable
- Alternate function input/output configurable

There are up to 35 general purpose I/O pins (GPIO) in GDEHC to implement logic input/output functions. Each of the GPIO ports has related control and configuration registers to satisfy the requirements of specific applications. The GPIO ports are pin-shared with other alternative functions (AFs) to obtain maximum flexibility on the package pins. Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current capable except for analog inputs.

3.4. Power saving modes

The GDSCN supports four types of device level and three types of module level power saving modes, device level power saving modes including MOD0, MOD1, MOD2 and MOD3, module level power saving modes including EtherCAT clock management, PHY power management and the LED pins power management. These modes reduce the power consumption and allow the application to achieve the best tradeoff among the conflicting demands of device operating time, speed and power consumption.

The device supports three types of module level power saving modes:

- The ECATCLKDIS bit in PMU_CTL0 register can use to disable EtherCAT core clock.
- PHY power management
 - PHY A and B ED power down management, support auto ED power down.
 - Common power down management.
- LEDs output management
 - The LEDOUTDIS bit in PMU_CTL0 register can use to disable LEDs output.
 - The LEDMODCFG bit in PMU_CTL0 register can use to configure LEDs working mode (take effect only when LEDOUTDIS is set).
 - The LEDINACT bit in PMU_CTL0 register can use to configure the inactive state when LEDs work in push-pull mode (take effect only when LEDOUTDIS is set).

3.5. Timers and Free-Running Counter (TIMER and FRC)

- 16-bit down counter
- Generate periodic system interrupts
- Resolution is 100us

The basic timer module has a 16-bit counter that can be used as an unsigned counter. The basic timer can be configured to generate interrupts. The resolution of basic timer is 100 μ s.

The Free-Running Counter has a 32-bit counter that can be used as an unsigned counter. The counter clock is 25MHz.

- 32-bit up counter
- Driven by free running 25Mhz clock

3.6. Process Data Interface (PDI) Wrapper

- Support SPI slave and EXMC mode.
- Supports three types SPI, QSPI, OSPI slave.
- EXMC supports both async and sync modes, 8-bit and 16-bit.

The Process Data Interface (PDI) Wrapper realizes the connection between ESC system bus and ESC core. through the AHB2OPB to connect. The SPI SLAVE and EXMC have only one work at the same time, which is selected by the pad of IO16(MCU_PDITYPE).

3.7. Ethernet PHYS

- Two internal phys connect to ESC core
- Supports MII interfaces, Auto negotiation and parallel detection capability for automatic speed and duplex selection

The GDSCN contains PHYs A and B, there are identical in functionality. The PHY A connects to the EtherCAT port 0 or 2. The PHY B connects to EtherCAT port 1. These PHYs interface with their respective MAC via an internal MII interface. The PHYs comply with the IEEE 802.3 Physical Layer for Twisted Pair Ethernet and can be configured for full duplex 100 Mbps (100BASE-TX / 100BASE-FX) Ethernet operation. All PHYs registers follow the IEEE 802.3 specified MII management register set and are fully configurable.

3.8. Package and operation temperature

- QFN64 (GDSCN832R2U6).
- Operation temperature range: -40°C to +85°C (industrial level).

4. Electrical characteristics

4.1. Absolute maximum ratings

The maximum ratings are the limits to which the device can be subjected without permanently damaging the device. Note that the device is not guaranteed to operate properly at the maximum ratings. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

Table 4-1. Absolute maximum ratings⁽¹⁾⁽³⁾

Symbol	Parameter	Min	Max	Unit
V _{DD1Ax}	Analog 1.1V power for Ethernet PHY	V _{SS} - 0.3	V _{SS} + 1.21	V
V _{OSCVDD11}	Internal 1.1V oscillator supply voltage	V _{SS} - 0.3	V _{SS} + 1.21	V
V _{CORE}	Digital core supply voltage	V _{SS} - 0.3	V _{SS} + 1.21	V
V _{DD3Ax}	Analog 3.3V power for Ethernet PHY ⁽²⁾	V _{SS} - 0.3	V _{SS} + 3.6	V
V _{DD33}	Supply voltage for the internal regulators ⁽²⁾	V _{SS} - 0.3	V _{SS} + 3.6	V
V _{DDIO}	IO supply voltage ⁽²⁾	V _{SS} - 0.3	V _{SS} + 3.6	V
V _{OSCI}	oscillator supply voltage	V _{SS} - 0.3	V _{SS} + 3.6	V
V _{IN}	Input voltage on 5VT I/O ⁽⁴⁾	V _{SS} - 0.3	V _{DDIO} + 3.6	V
	Input voltage on other I/O	V _{SS} - 0.3	V _{DD} + 0.3	
T _A	Operating temperature range	-40	85	°C
P _D	Power dissipation at T _A = 85°C of QFN64	—	169	mW
T _{STG}	Storage temperature range	-65	150	°C
T _J	Maximum junction temperature	—	125	°C

(1) Value guaranteed by design, not 100% tested in production.

(2) All main power and ground pins should be connected to an external power source within the allowable range.

(3) The device junction temperature must be kept below maximum T_J.

(4) V_{IN} maximum value cannot exceed 5.5 V.

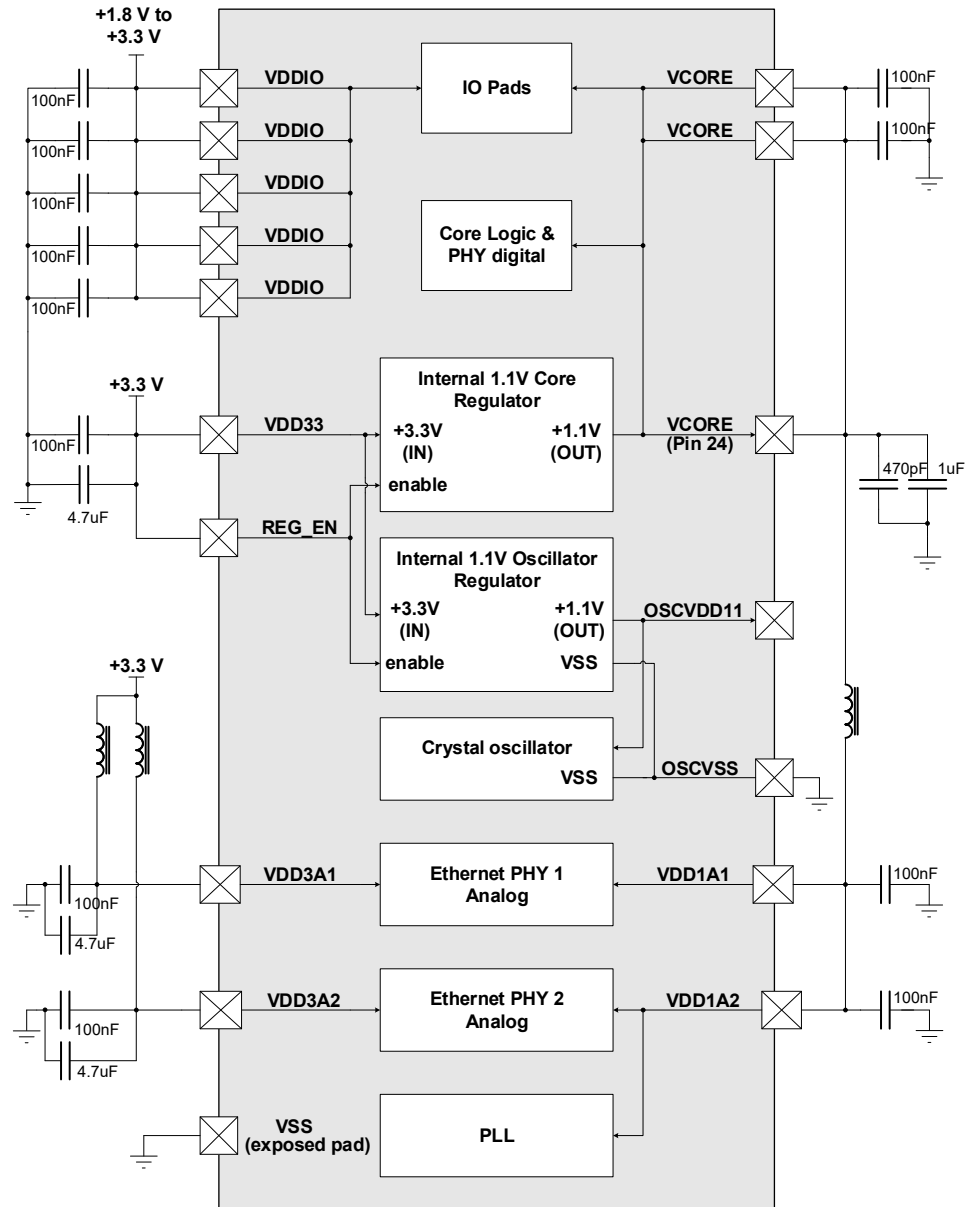
4.2. Recommended DC characteristics

Table 4-2. DC operating conditions

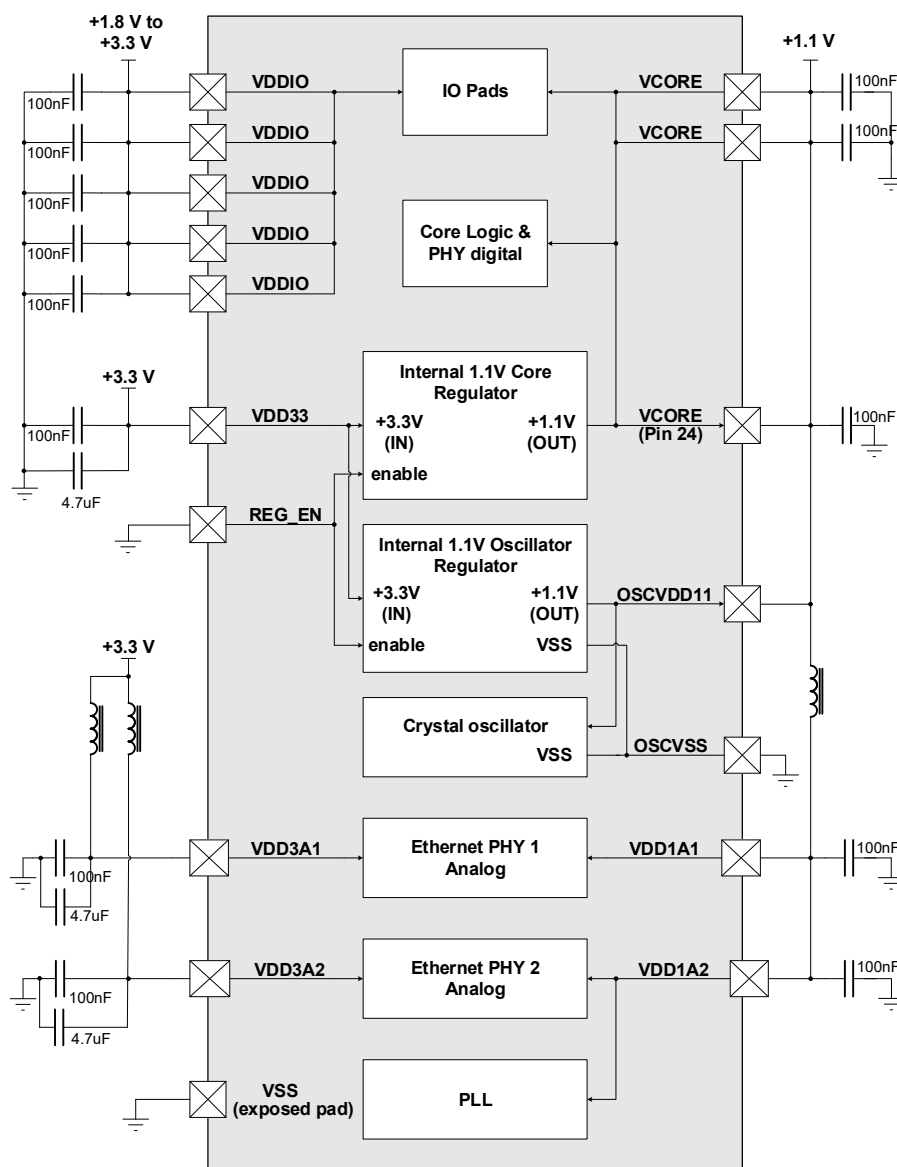
Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
V _{DD1Ax}	Analog 1.1V power for Ethernet PHY	—	1.05	1.1	1.15	V
V _{OSCVDD11}	Internal 1.1V oscillator supply voltage	—	1.0	1.1	1.2	V
V _{CORE}	Digital core supply voltage	—	1.05	1.1	1.15	V
V _{DD3Ax}	Analog 3.3V power for Ethernet PHY	—	3.0	3.3	3.6	V
V _{DD33}	Supply voltage for the internal regulator	—	3.0	3.3	3.6	V
V _{DDIO}	IO supply voltage	—	1.8	3.3	3.6	V

(1) Value guaranteed by characterization, not 100% tested in production.

Figure 4-1. Recommended power connections(regulators enabled)⁽¹⁾



(1) All decoupling capacitors need to be as close as possible to the pins on the PCB board.

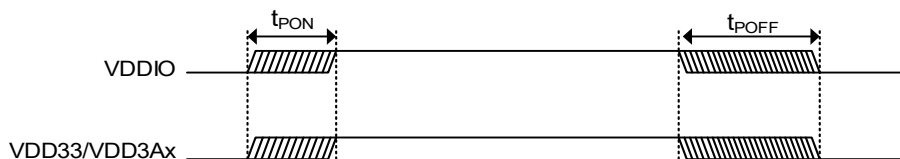
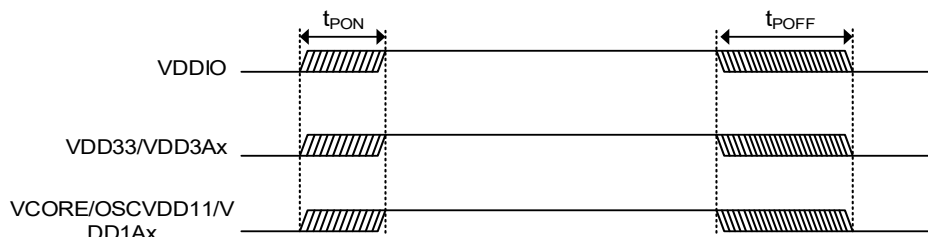
Figure 4-2. Recommended power connections(regulators disabled)⁽¹⁾


(1) All decoupling capacitors need to be as close as possible to the pins on the PCB board.

Table 4-3. Power supply on and off timing values⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _{PON}	Power supply turn on time	—	—	—	50	ms
t _{POFF}	Power supply turn off time	—	—	—	500	ms

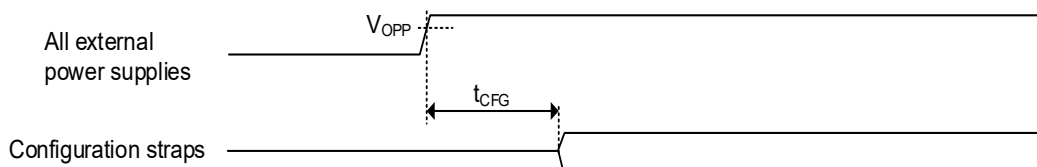
(1) Value guaranteed by design, not 100% tested in production.

Figure 4-3. Power supply on and off timing (internal regulators)

Figure 4-4. Power supply on and off timing (external regulators)

Table 4-4. Power-on configuration strap latching timing values⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _{CFG}	Configuration strap valid time	—	—	—	15	ms

(1) Value guaranteed by design, not 100% tested in production.

(2) Configuration straps must only be pulled high or low. Configuration straps must not be driven as inputs.

Figure 4-5. Power-on configuration strap latching timing diagram


4.3. EMC characteristics

Component level ESD include HBM (Human body model, according to ANSI/ESDA/JEDEC JS-001) and CDM (ANSI/ESDA/JEDEC JS-002), that ESD field events during manufacturing in an ESD protected area, such as PCB assembly/repair, IC assembly/test and Fab environment. The ESD protected area (EPA) has many measures, for instance ESD protective packaging, grounding person wrist strap to ground (or flooring/footwear), grounded work surface and ionizer.

Static latch-up (LU, according to JEDEC78) test is based on the two measurement methods, I/O current injection value (I-test) and power supply over-voltage value.

Table 4-5. Component level ESD and latch-up characteristics ⁽¹⁾

Symbol	Description	Conditions	Package	Max	Unit	Level
V _{HBM}	Human body model electrostatic discharge voltage (Any pin combination)	T _J = 25 °C; JS-001-2017	QFN64	TBD	V	TBD
V _{CDM}	Charge device model electrostatic discharge voltage (All pins)	T _J = 25 °C; JS-002-2018	QFN64	TBD	V	TBD
LU	I-test	T _A = 125 °C, JESD78F	QFN64	TBD	mA	TBD
	V _{supply} over voltage			TBD	V	

(1) Value guaranteed by characterization, not 100% tested in production.

4.4. Power consumption

Table 4-6. Power consumption characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Regulators enabled						
3.3V Device Current ⁽²⁾	Supply current (MOD0)	Disconnect to the Ethernet cable	—	36	—	mA
		100BASE-TX with traffic	—	86	—	
		100BASE-TX with idle	—	85	—	
	Supply current (MOD1)	100BASE-TX with idle	—	82	—	
	Supply current (MOD2)	100BASE-TX with idle	—	80	—	
	Supply current (MOD3)	All clocks off	—	17	—	
Regulators disabled						
3.3V Device Current ⁽²⁾	Supply current (MOD0)	Disconnect to the Ethernet cable	—	24	—	mA
		100BASE-TX with traffic	—	42	—	
		100BASE-TX with idle	—	42	—	
	Supply current (MOD1)	100BASE-TX with idle	—	40	—	
	Supply current (MOD2)	100BASE-TX with idle	—	40	—	
	Supply current (MOD3)	All clocks off	—	16	—	
1.1V Device Current ⁽³⁾	Supply current (MOD0)	Disconnect to the Ethernet cable	—	8	—	mA
		100BASE-TX with traffic	—	44	—	
		100BASE-TX with idle	—	44	—	
	Supply current (MOD1)	100BASE-TX with idle	—	42	—	
	Supply current (MOD2)	100BASE-TX with idle	—	40	—	

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
	Supply current (MOD3)	All clocks off	—	0	—	

- (1) Value guaranteed by sample, not 100% tested in production.
(2) Including the following pins, VDD33,VDD3Ax,VDDIO.
(3) Including the following pins, OSCVDD11,VDD1Ax,VCORE.

4.5. I/O characteristics

Table 4-7. Non-variable I/O DC electrical characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Analog input buffer(RXPA/RXNA/RXPB/RXNB)						
V _{IN_DIFF}	Differential input level	—	—	2	—	V
V _{CM}	Common mode voltage		—	1.65	—	
C _{IN}	Input capacitance		—	3.27	—	
Crystal oscillator input buffer(OSCI input)						
V _{ILI}	Low input level	—	-0.3	—	0.35	V
V _{IHI}	High input level		OSCVDD11-0.35	—	3.6	
Low voltage PECL input buffer						
V _{IL}	Low input level	—	-0.3	—	0.8	V
V _{IH}	High input level		2	—	3.93	
Low voltage PECL output buffer						
V _{OL}	Low input level	—	—	—	0.4	V
V _{OH}	High input level		2.4	—	—	
C _{LOAD}	Load capacitance		—	—	1.1	—

- (1) Value guaranteed by design, not 100% tested in production.

Table 4-8. Variable I/O DC electrical characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ		Max	Unit
				1.8V	3.3V		
Schmitt-triggered input buffer							
V _{ILI}	Low input level	—	-0.3	—	—	—	V
V _{IHI}	High input level		—	—	—	3.6	
V _{ILT}	Negative-going threshold		0.65	0.8	1.47	1.75	
V _{IHT}	Positive-going threshold		0.81	0.96	1.61	1.88	
V _{HYS}	Schmitt trigger hysteresis (V _{IHT} - V _{ILT})		120	150	145	210	mV
I _{IH}	Input leakage (V _{IN} = VSS or VDDIO)		-10	—	—	10	uA
C _{IN}	Input capacitance		—	5	5	7	pF
R _{PU}	Weak pull-up equivalent resistor (V _{IN} = VSS)		57.6	68	68	80	kΩ
I _{PU}	Pull-up current (V _{IN} = VSS)		62.5	26	48	20.25	uA
R _{PD}	Weak pull-down equivalent resistor (V _{IN} = VDD33)		57.5	68	68	80.1	kΩ
I _{PD}	Pull-down current (V _{IN} = VDD33)	62.6	26	48	20.2	uA	
Variable voltage output with 8 mA sink and 8 mA source buffers							
V _{OL}	Low output level	I _{load} = 8mA	—	—	—	0.4	V
V _{OH}	High output level	I _{load} = -8mA	VDDIO - 0.4	—	—	—	
Variable voltage open-drain output with 8 mA sink buffers							
V _{OL}	Low output level	I _{load} = 8mA	—	—	—	0.4	V
Variable voltage output with 12 mA sink and 12 mA source buffers							
V _{OL}	Low output level	I _{load} = 12mA	—	—	—	0.4	V
V _{OH}	High output level	I _{load} = -12mA	VDDIO - 0.4	—	—	—	
Variable voltage open-drain output with 12 mA sink buffers							
V _{OL}	Low output level	I _{load} = 12mA	—	—	—	0.4	V
Variable voltage open-source output with 12 mA source buffers							
V _{OH}	High output level	I _{load} = -12mA	VDDIO -0.4	—	—	—	V

(1) Value guaranteed by design, not 100% tested in production.

Table 4-9. 100base-TX transceiver characteristics⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
$V_{PPH}^{(2)}$	Peak differential output voltage high	950	—	1050	mVpk
$V_{PPL}^{(2)}$	Peak differential output voltage low	-950	—	-1050	mVpk
$V_{SS}^{(2)}$	Signal amplitude symmetry	98	—	102	%
$T_{RF}^{(2)}$	Signal rise and fall time	3	—	5	ns
$T_{RFS}^{(2)}$	Rise and fall symmetry	—	—	0.5	ns
D_{CD}	Duty cycle distortion	—	—	0.5	ns
V_{OS}	Overshoot and undershoot	—	—	5	%
—	Jitter	—	—	1.4	ns

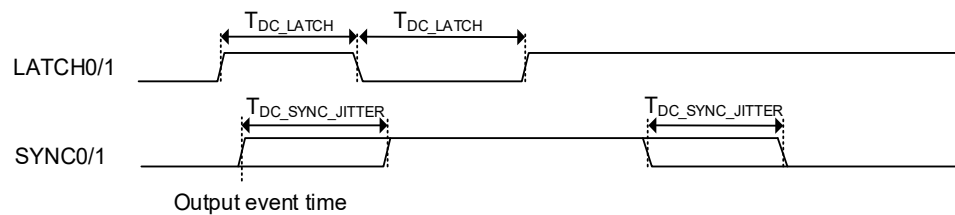
(1) Value guaranteed by characterization, not 100% tested in production.

(2) Measured at line side of transformer, line replace by 100ohm($\pm 1\%$) resistor.

Table 4-10. EtherCAT SYNC/LATCH timing values⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{DC_LATCH}	Time between LATCH0 or LATCH1 events	—	15	—	—	ns
$t_{DC_SYNC_JITTER}$	SYNC0 or SYNC1 output jitter	—	—	—	15	ns

(1) Value guaranteed by characterization, not 100% tested in production.

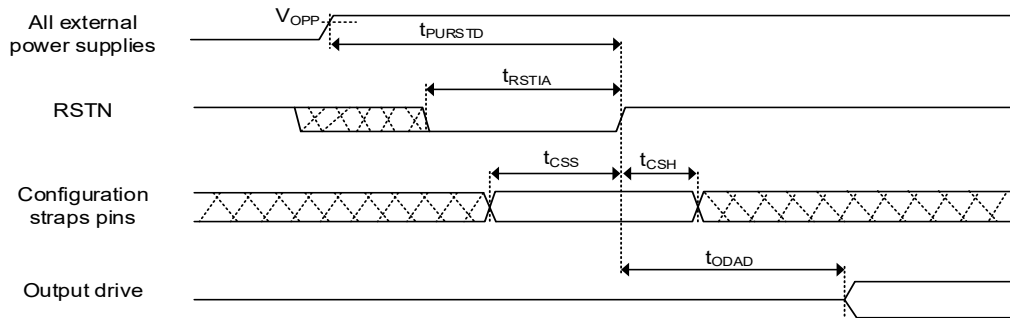
Figure 4-6. EtherCAT SYNC/LATCH timing diagram


4.6. RSTN pin characteristics

Table 4-11. RSTN pin configuration strap latching timing values⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{PURSTD}	External power supplies at operational level to RSTN invalid time	—	25	—	—	ms
t_{RSTIA}	RSTN input valid time	—	200	—	—	us
T_{CSS}	Configuration strap pins setup time to RSTN invalid	—	200	—	—	ns
t_{CSH}	Configuration strap pins hold time after RSTN invalid	—	30	—	—	ns
t_{ODAD}	Output drive time after RSTN invalid	—	3	—	—	us

(1) Value guaranteed by design, not 100% tested in production.

Figure 4-7. Power-on configuration strap latching timing diagram


4.7. Clock characteristics

Table 4-12. Crystal specifications⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
Crystal cut		AT, typ			
Crystal oscillation mode		Fundamental mode			
Crystal calibration mode		Parallel resonant mode			
F _{FUND}	Frequency	—	25.000	—	MHZ
F _{TOL}	802.3 Frequency tolerance at 25°C	—	—	±40	ppm
F _{TEMP}	802.3 Frequency stability over temp	—	—	±40	ppm
F _{AGE}	802.3 Frequency deviation over time	—	±3 ~ 5	—	ppm
802.3 total allowable PPM budget		—	—	±50	ppm
F _{TOL}	EtherCAT frequency tolerance at 25°C	—	—	±15	ppm
F _{TEMP}	EtherCAT frequency stability over Temp	—	—	±15	ppm
F _{AGE}	EtherCAT frequency deviation over Time	—	±3 ~ 5	—	ppm
EtherCAT total allowable PPM budget		—	—	±25	ppm
C _O	Parallel Capacitance	—	—	7	pF
C _L	Recommended matching capacitance on OSCI and OSCO	—	10	20	pF
R ₁	Equivalent Series Resistance	—	—	100	Ω
Operating Temperature Range		-40	—	125	°C
OSCI Pin Capacitance		—	3	—	pF
OSCO Pin Capacitance		—	3	—	pF

(1) Value guaranteed by design, not 100% tested in production.

4.8. Digital I/O characteristics

Table 4-13. EtherCAT I/O timing values⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
$t_{\text{INDATASYNCS}}$	Input data setup to SYNC0/1 rising	10	—	—	ns
$t_{\text{INDATASYNCH}}$	Input data hold from SYNC0/1 rising	0	—	—	ns
$t_{\text{INDATALATCHS}}$	Input data setup to LATCH_IN rising	8	—	—	ns
$t_{\text{INDATALATCHH}}$	Input data hold from LATCH_IN rising	4	—	—	ns
t_{LATCHIN}	LATCH_IN rising	8	—	—	ns
$t_{\text{LATCHINDELAY}}$	Time between consecutive input events	440	—	—	ns
t_{SOF}	SOF high time	35	—	—	ns
t_{SOFDATAV}	Input data valid after SOF active, so that input data can be read in the same frame	—	—	1.2	us
t_{SOFDATAH}	Input data hold after SOF active, so that input data can be read in the same frame	1.6	—	—	us
t_{OUTDATAS}	Output data setup to OUTVALID rising	65	—	—	ns
t_{OUTDATAH}	Output data hold from OUTVALID falling	65	—	—	ns
t_{OUTVALID}	OUTVALID high time	75	—	—	ns
$t_{\text{OUTVALIDDELAY}}$	Time between consecutive output events	320	—	—	ns
t_{EOF}	EOF high time	35	—	45	ns
t_{EOFDATA}	Output data valid after EOF	—	—	35	ns
$t_{\text{WD_TRIG}}$	WD_TRIG high time	35	—	45	ns
$t_{\text{WD_TRIGDATA}}$	Output data valid after WD_TRIG	—	—	35	ns
t_{SYNCDATA}	Output data valid after SYNC0/1	—	—	25	ns
$t_{\text{OE_EXTDATA}}$	OE_EXT to data low	0	—	15	ns
$t_{\text{BIDIRDELAY}}$	Time between consecutive input or output events	440	—	—	ns

(1) Value guaranteed by design, not 100% tested in production.

Figure 4-8. EtherCAT digital I/O input timing diagram

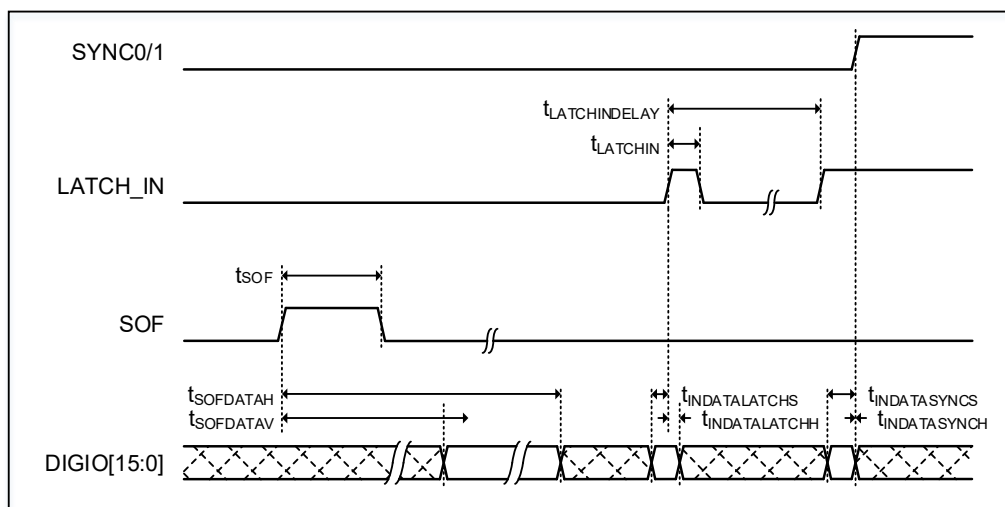


Figure 4-9. EtherCAT digital I/O output timing diagram

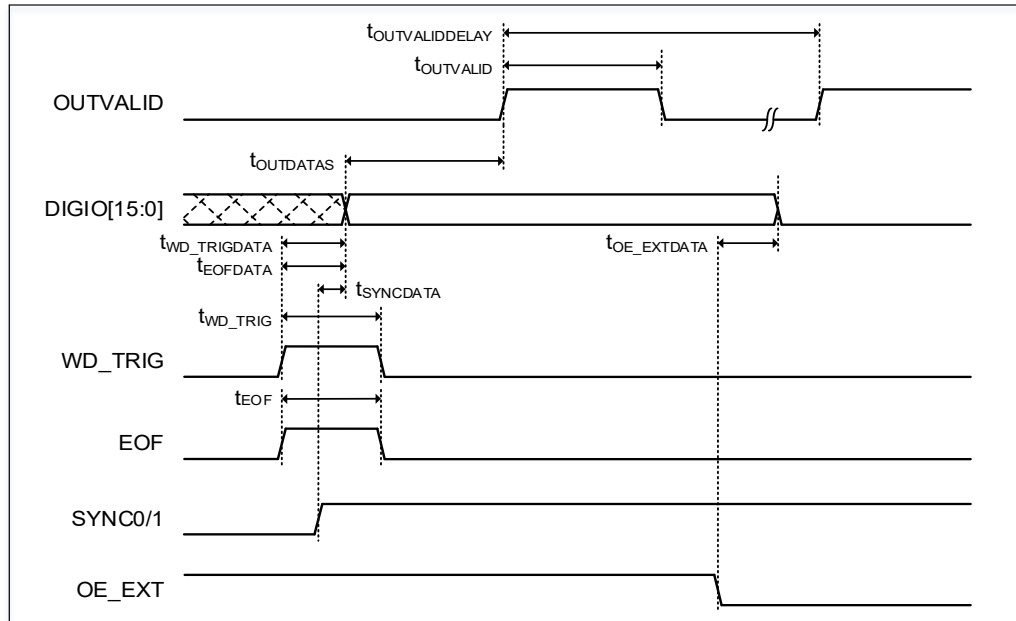
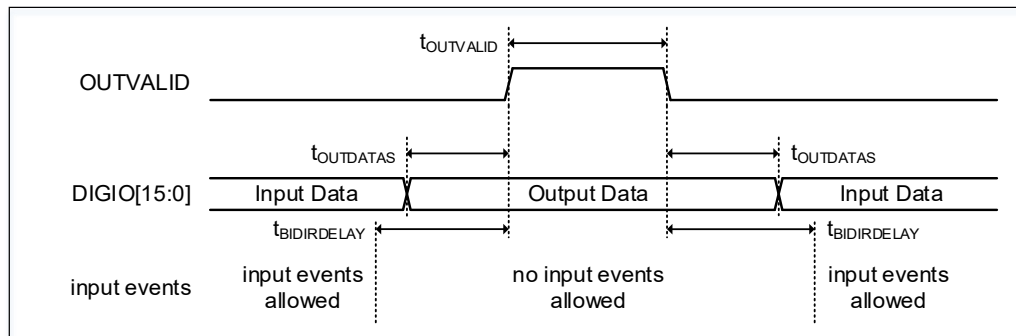


Figure 4-10. EtherCAT digital I/O bi-directional timing diagram



4.9. I2C characteristics

Table 4-14. I2C controller timing values⁽¹⁾

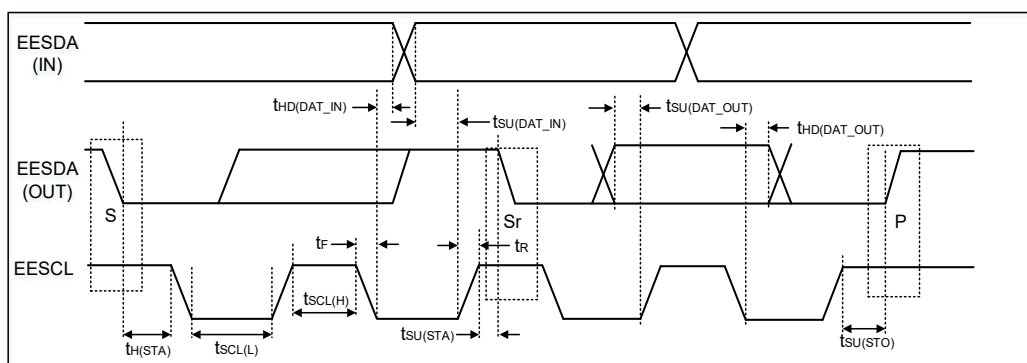
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCL}	EESCL clock frequency	—	—	148.8	—	KHz
$t_{SCL(H)}$	EESCL clock high time	—	3.0	—	—	us
$t_{SCL(L)}$	EESCL clock low time	—	3.0	—	—	us
$t_{r(SDA/SCL)}$	EESDA and EESCL rise time	—	—	—	300	ns
$t_{f(SDA/SCL)}$	EESDA and EESCL fall time	—	—	—	300	ns
$t_{SU(STA)}^{(2)}$	Setup time (provided to target) of EESCL high before EESDA output falling for repeated start condition	—	1000	—	—	ns
$t_{HD(STA)}^{(2)}$	Hold time (provided to target) of EESCL after EESDA output falling for start or repeated start condition	—	1000	—	—	ns
$t_{SU(DAT_IN)}^{(3)}$	Setup time (from target) EESDA input before EESCL rising	—	200	—	—	ns
$t_{HD(DAT_IN)}$	Hold time (from target) of EESDA input after EESCL falling	—	0	—	—	ns
$t_{SU(DAT_OUT)}^{(3)}$	Setup time (provided to target) EESDA output before EESCL rising	—	400	—	—	ns
$t_{HD(DAT_OUT)}^{(3)}$	Hold time (provided to target) of EESDA output after EESCL falling	—	400	—	—	ns
$t_{SU(STO)}^{(2)}$	Setup time (provided to target) of EESCL high before EESDA output rising for stop condition	—	1000	—	—	ns

(1) Guaranteed by design, not 100% tested in production.

(2) These values provide 400ns of margin compared to the I2C fast-mode specification.

(3) These values provide a margin of approximately 2100ns compared to the I2C fast-mode specification.

Figure 4-11. I2C bus timing diagram



4.10. SPI /QSPI/OSPI slave characteristics

Table 4-15. SPI/SQI/OSPI slave timing values ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK}	SCK clock frequency	—	—	—	100	MHz
t_{HIGH}	SCK high time	—	—	5	—	ns
t_{LOW}	SCK low time	—	—	5	—	ns
t_{SCSS}	SCS setup time to SCK	—	5	—	—	ns
t_{SCSH}	SCS hold time from SCK	—	5	—	—	ns
t_{SCSHL}	SCS inactive time	—	—	50	—	ns
t_{SU}	Data input setup time to SCK	—	2	—	—	ns
t_{HD}	Data input hold time from SCK	—	3	—	—	ns
t_{ON}	Data output turn on time from SCK	—	0	—	—	ns
t_v	Data output valid time from SCK	—	—	—	8	ns
t_{HO}	Data output hold time from SCK	—	0	—	—	ns
t_{DIS}	Data output disable time from SCS inactive	—	—	—	20	ns

(1) Value guaranteed by design, not 100% tested in production.

Figure 4-12. SPI/QSPI/OSPI input timing diagram

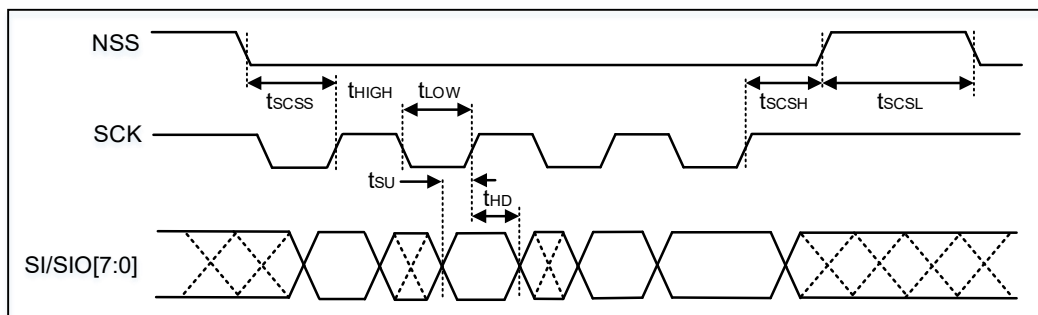
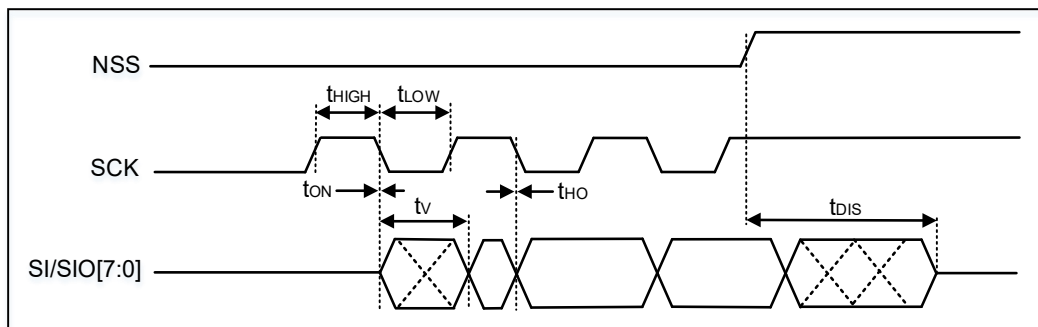


Figure 4-13. SPI/QSPI/OSPI output timing diagram



4.11. EXMC characteristics

Table 4-16. Synchronous multiplexed read timings⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
f_{CLK}	EXMC clock frequency	—	—	80	MHz
$t_{su}(NE_CLKH)$	EXMC_NE low setup time to EXMC_CLK high	3.25	—	—	ns
$t_{su}(NL_CLKH)$	EXMC_NL low setup time to EXMC_CLK high	4	—	—	ns
$t_{su}(NOEL_CLKH)$	EXMC_NOE low setup time to EXMC_CLK high	3.75	—	—	ns
$t_{su}(ADV_CLKH)$	EXMC_ADV setup time to EXMC_CLK high	3	—	—	ns
$t_d(CLKH_DV)$	EXMC_CLK high valid time to EXMC_DV	—	—	9.5	ns
$t_d(CLKH_DIV)$	EXMC_CLK high valid time to EXMC_DIV	0	—	—	ns
$t_d(CLKH_NWAITL)$	EXMC_CLK high valid time to EXMC_NWAIT low	—	—	9	ns
$t_d(CLKH_NWAITH)$	EXMC_CLK high valid time to EXMC_NWAIT high	2.5	—	—	ns

(1) Value guaranteed by design, not 100% tested in production.

Figure 4-14. Synchronous multiplexed read timings diagram

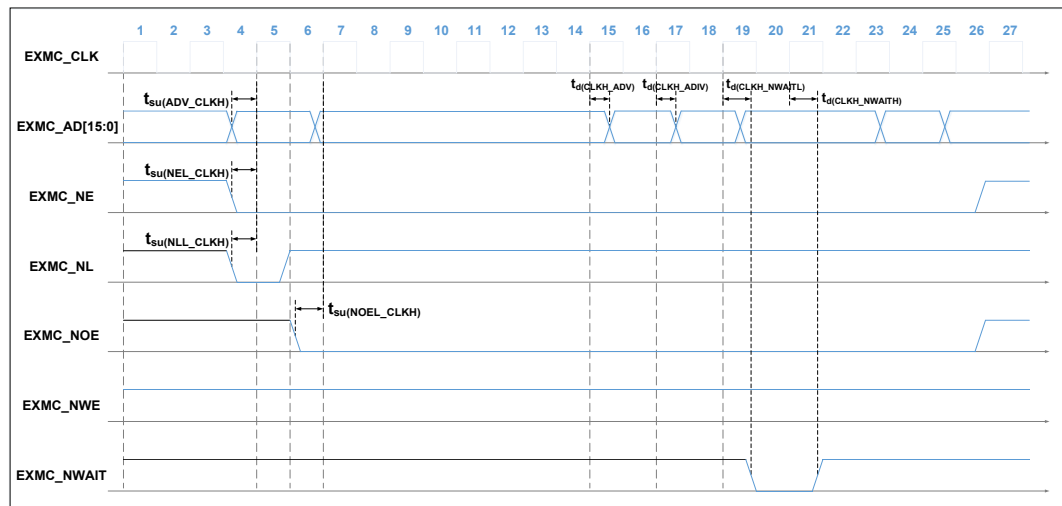
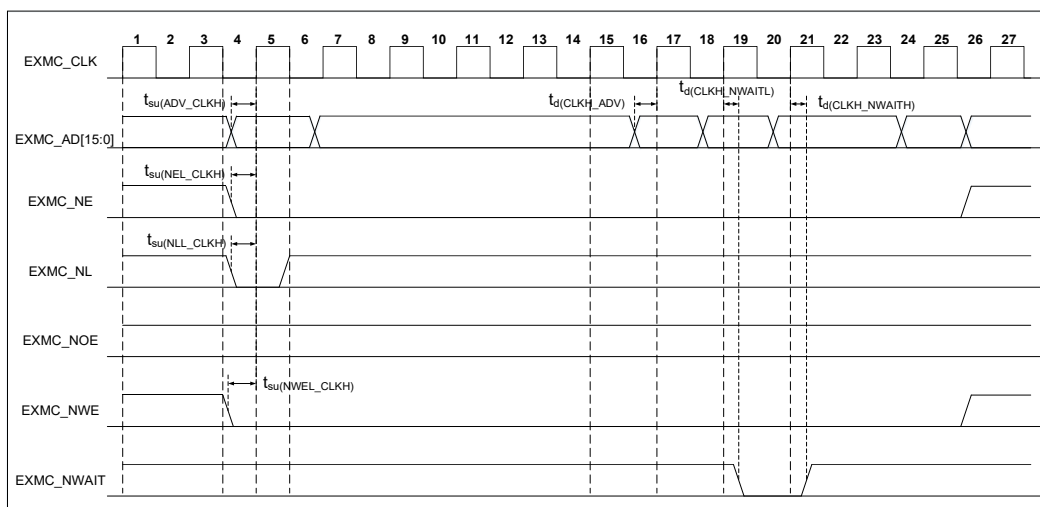


Table 4-17. Synchronous multiplexed write timings⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
f_{CLK}	EXMC clock frequency	—	—	80	MHz
$t_{su}(NL_CLKH)$	EXMC_NL low setup time to EXMC_CLK high	3.25	—	—	ns
$t_{su}(NWE_CLKH)$	EXMC_NWE low setup time to EXMC_CLK high	4	—	—	ns
$t_{su}(ADV_CLKH)$	EXMC_ADV setup time to EXMC_CLK high	3.75	—	—	ns
$t_{su}(DV_CLKH)$	EXMC_DV setup time to EXMC_CLK high	3	—	—	ns
$t_d(DV_CLKH)$	EXMC_DV high valid time to EXMC_CLK	3.25	—	—	ns
$t_d(CLKH_NWAITL)$	EXMC_CLK high valid time to EXMC_NWAIT low	—	—	9	ns
$t_d(CLKH_NWAITH)$	EXMC_CLK high valid time to EXMC_NWAIT high	2.5	—	—	ns

(1) Value guaranteed by design, not 100% tested in production.

Figure 4-15. Synchronous multiplexed write timings diagram


4.12. Ethernet PHY characteristics

Table 4-18. MII TX timing values⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
t_{CLKP}	MII_CLK25 period	40	—	—	ns
t_{CLKH}	MII_CLK25 high time	18	—	22	ns
t_{CLKL}	MII_CLK25 low time	18	—	22	ns
t_{VAL}	MII_TXD[3:0], MII_TXEN output valid from rising edge of MII_CLK25	—	—	10	ns
t_{HOLD}	MII_TXD[3:0], MII_TXEN output hold from rising edge of MII_CLK25	0	—	—	ns

(1) Value guaranteed by design, not 100% tested in production.

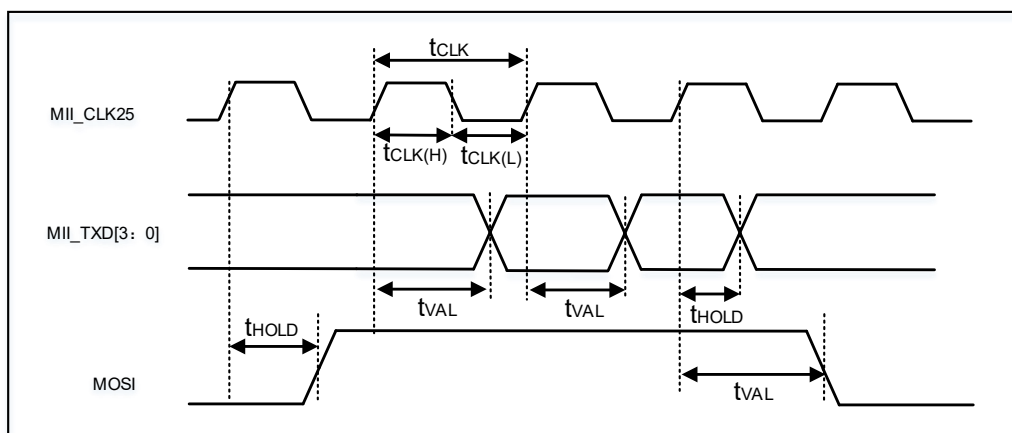
Figure 4-16. MII TX timing diagram


Table 4-19. MII RX timing values⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
t_{CLKP}	MII_RXCLK period	40	—	—	ns
t_{CLKH}	MII_RXCLK high time	16	—	24	ns
t_{CLKL}	MII_RXCLK low time	16	—	24	ns
t_{SU}	MII_RXD[3:0], MII_RXER, MII_RXDV setup time to rising edge of MII_RXCLK	5	—	—	ns
t_{HOLD}	MII_RXD[3:0], MII_RXER, MII_RXDV hold time after rising edge of MII_RXCLK	6	—	—	ns

(1) Value guaranteed by design, not 100% tested in production.

Figure 4-17. MII RX timing diagram

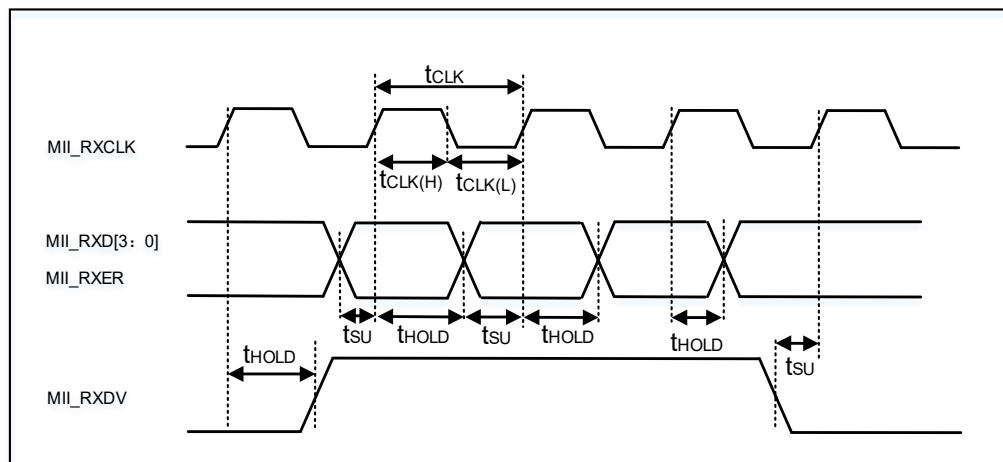
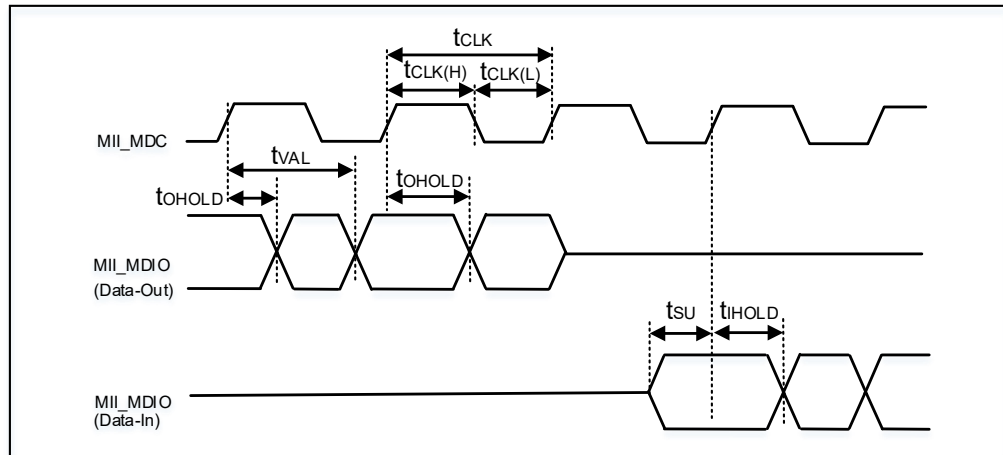


Table 4-20. Management access timing values⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
t_{CLKP}	MII_MDC period	400	—	—	ns
t_{CLKH}	MII_MDC high time	180	—	—	ns
t_{CLKL}	MII_MDC low time	180	—	—	ns
t_{VAL}	MII_MDIO output valid from rising edge of MII_MDC	—	—	250	ns
t_{HOLD}	MII_MDIO output hold from rising edge of MII_MDC	150	—	—	ns
t_{SU}	MII_MDIO input setup time to rising edge of MII_MDC	70	—	—	ns
t_{iHOLD}	MII_MDIO input hold time after rising edge of MII_MDC	0	—	—	ns

(1) Value guaranteed by design, not 100% tested in production.

Figure 4-18. Management access timing diagram



5. Package information

5.1. QFN64 package outline dimensions

Figure 5-1. QFN64 package outline

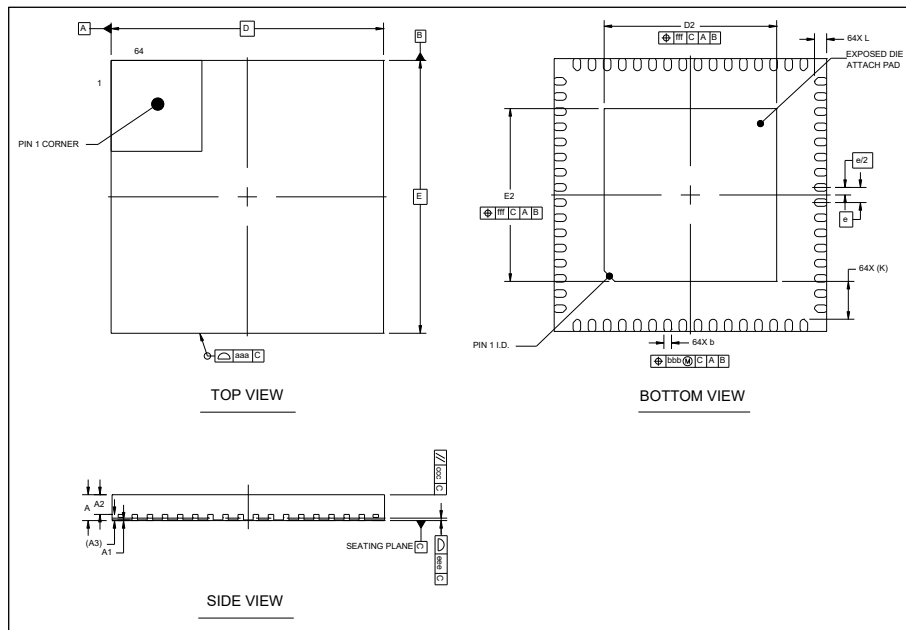
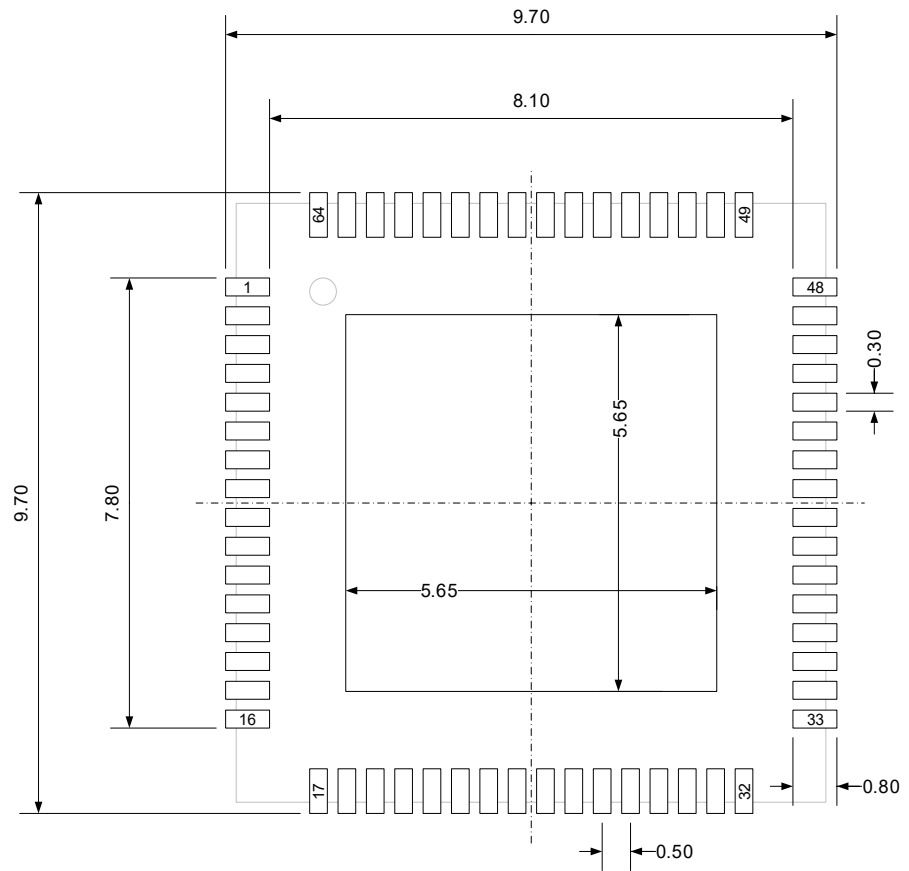


Table 5-1. QFN64 package dimensions

Symbol	Min	Typ	Max
A	0.80	0.85	0.90
A1	0	0.02	0.05
A2	—	0.65	—
A3	—	0.203	—
b	0.20	0.25	0.30
D	—	9.00	—
D2	5.60	5.70	5.80
E	—	9.00	—
E2	5.60	5.70	5.80
e	—	0.50	—
K	—	1.25	—
L	0.30	0.40	0.50
aaa	—	0.10	—
bbb	—	0.10	—
ccc	—	0.10	—
eee	—	0.08	—
fff	—	0.10	—

(Original dimensions are in millimeters)

Figure 5-2. QFN64 recommended footprint



(Original dimensions are in millimeters)

5.2. Thermal characteristics

Thermal resistance is used to characterize the thermal performance of the package device, which is represented by the Greek letter “ θ ”. For semiconductor devices, thermal resistance represents the steady-state temperature rise of the chip junction due to the heat dissipated on the chip surface.

θ_{JA} : Thermal resistance, junction-to-ambient.

θ_{JB} : Thermal resistance, junction-to-board.

θ_{JC} : Thermal resistance, junction-to-case.

Ψ_{JB} : Thermal characterization parameter, junction-to-board.

Ψ_{JT} : Thermal characterization parameter, junction-to-top center.

$$\theta_{JA}=(T_J-T_A)/P_D \quad (5-1)$$

$$\theta_{JB}=(T_J-T_B)/P_D \quad (5-2)$$

$$\theta_{JC}=(T_J-T_C)/P_D \quad (5-3)$$

Where, T_J = Junction temperature.

T_A = Ambient temperature

T_B = Board temperature

T_C = Case temperature which is monitoring on package surface

P_D = Total power dissipation

θ_{JA} represents the resistance of the heat flows from the heating junction to ambient air. It is an indicator of package heat dissipation capability. Lower θ_{JA} can be considerate as better overall thermal performance. θ_{JA} is generally used to estimate junction temperature.

θ_{JB} is used to measure the heat flow resistance between the chip surface and the PCB board.

θ_{JC} represents the thermal resistance between the chip surface and the package top case. θ_{JC} is mainly used to estimate the heat dissipation of the system (using heat sink or other heat dissipation methods outside the device package).

Table 5-2. Package thermal characteristics⁽¹⁾

Symbol	Condition	Package	Value	Unit
θ_{JA}	Natural convection, 2S2P PCB	QFN64	23.7	°C/W
θ_{JB}	Cold plate, 2S2P PCB	QFN64	10	°C/W
θ_{JC}	Cold plate, 2S2P PCB	QFN64	18	°C/W
Ψ_{JB}	Natural convection, 2S2P PCB	QFN64	10	°C/W
Ψ_{JT}	Natural convection, 2S2P PCB	QFN64	0.8	°C/W

(1): Thermal characteristics are based on simulation, and meet JEDEC specification.

6. Ordering information

Table 6-1. Part ordering code for GDSCN832xx devices

Ordering code	Package	Package type	Temperature operating range
GDSCN832R2U6	QFN64	Green	Industrial -40 °C to +85 °C

7. Revision history

Table 7-1. Revision history

Revision No.	Description	Date
1.0	Initial Release	Nov.8, 2024

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